ABSTRACT OF THE DISCLOSURE

In a nonvolatile semiconductor memory device including a nonvolatile cell circuit, a step-up circuit receives a clock signal to generate a step-up voltage for the nonvolatile cell circuit. A voltage divider divides the step-up voltage to generate a plurality of voltages. A selector selects one of the voltages. A reference voltage generating circuit generates a reference voltage. A first comparator compares the selected one of the voltages with the reference voltage. A gate circuit supplies the clock signal to the step-up circuit in accordance with an output signal of the first comparator so that the selected one of the voltages is brought close to the reference voltage. Also, a second comparator compares the step-up voltage with an externally-provided expected value. A counting signal generating circuit generates a counting signal in accordance with an output signal of the first comparator. A counter changes a value thereof by receiving the counting signal. Thus, the selector selects the one of the voltages in accordance with the value of the counter, so that the step-up voltage is brought close to the expected value.